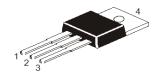
Plastic Power Transistor







Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector

Feature:

• Complementary Silicon Transistors Intended for a Wide Variety of Switching and Amplifier Applications, Series and Shunt Regulators, Driver and Output Stages of Hi-Fi Amplifiers

Absolute Maximum Ratings ($T_a = 25$ °C):

Description	Symbol	TIP41C	Unit	
Collector Emitter Voltage	V _{CEO}	100		
Collector Base Voltage	V _{CBO}	100	V	
Emitter Base Voltage	V _{EBO}	5		
Collector Current Continuous	I _c	6		
Collector Current Peak	I _{CM}	10	А	
Base Current	I _B	2		
Power Dissipation upto T _c = 25°C Derate above 25°C		65 520	W	
Power Dissipation upto T _a = 25°C Derate above 25°C	P _D	2 16	mW/°C	
Unclamped Inductive Load Energy	*E	62.5	mJ	
Storage Temperature	ure T _{stg} 150		°C	
Junction Temperature	T _j	- 65 to +150	C	

Thermal Resistance

Junction to Case	R _{th (j-c)}	1.92	°C/W
Junction to Ambient in Free Air	R _{th (j-a)}	62.5	C/VV

^{*} I_c = 2.5A, L = 20mH, P.R.F. = 10Hz, V_{cc} = 10V, R_{BE} = 100 Ω

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro



Plastic Power Transistor



Electrical Characteristics ($T_C = 25$ °C unless specified otherwise):

Description	Symbol	Test Condition	Min.	Max.	Unit
Collector Emitter Voltage	*V _{CEO}	$I_{\rm C} = 30 {\rm mA}, I_{\rm B} = 0$	100	-	V
Collector Cut off Current	I _{CEO}	$V_{CE} = 60V, I_{B} = 0$	-	0.7	
Collector Cut off Current	I _{CES}	$V_{CE} = V_{CEO}$ (max.), $V_{BE} = 0$	-	0.4	mA
Emitter Cut off Current	I _{EBO}	$V_{EB} = 5V$, $I_C = 0$	-	1	
DC Current Gain	*h _{FE}	$I_{C} = 0.3A, V_{CE} = 4V$ $I_{C} = 3A, V_{CE} = 4V$	30 15	75	-
Collector Emitter Saturation Voltage	*V _{CE (sat)}	IC = 6A, IB = 0.6A	-	1.5	V
Base Emitter on Voltage	*V _{BE (on)}	IC = 6A, VCE =4 V	-	2	

^{*}Pulse Test : Pulse width ≤300µs, Duty Cycle ≤2%.

Dynamic Characteristics

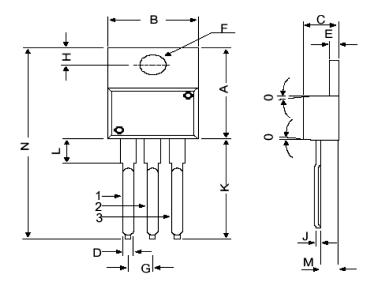
Description	Symbol	Test Condition	Min.	Max.	Unit
Small Signal Current Gain	h _{fe}	$I_{\rm C}$ = 0.5A, $V_{\rm CE}$ = 10V, f = 1kHz	20	-	-
Transition Frequency	f _T	I _C = 0.5A, V _{CE} = 10V, f = 1MHz	3	-	MHz

Switching Characteristics

Description	Symbol	Test Condition	Typical	Unit
Turn On Time	t _{on}	$V_{cc} = 30V$, $I_{c} = 6A$, $I_{B1} = I_{B2} = 0.6A$,	0.6	
Turn Off Time	t _{off}	$RL = 5\Omega$	1.4	μs

Plastic Power Transistor





Dimensions	Min.	Max.
Α	14.42	16.51
В	9.63	10.67
С	3.56	4.83
D	-	0.9
E	1.15	1.4
F	3.75	3.88
G	2.29	2.79
Н	2.54	3.43
J	-	0.56
K	12.7	14.73
L	2.8	4.07
M	2.03	2.92
N	-	31.24
0	7	0

Dimensions: Millimetres

Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector

Part Number Table

Description	Part Number	
Transistor, NPN, TO-220	TIP41C	

Important Notice: This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro

